

# Abdallah Ougazzaden

## List of Publications by Citations

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275  
ext. papers

4,491  
ext. citations

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L-index

#	Paper	IF	Citations
251	Optical properties of low band gap GaAs(1-x)Nx layers: Influence of post-growth treatments. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 1409-1411	3.4	158
250	Controlled crack propagation for atomic precision handling of wafer-scale two-dimensional materials. <i>Science</i> , <b>2018</b> , 362, 665-670	33.3	133
249	The 2020 UV emitter roadmap. <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 503001	3	123
248	Polarity governs atomic interaction through two-dimensional materials. <i>Nature Materials</i> , <b>2018</b> , 17, 999-1004	10.4	107
247	Metal organic vapor phase epitaxy growth of GaAsN on GaAs using dimethylhydrazine and tertiarybutylarsine. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 2861-2863	3.4	90
246	Use of ZnO thin films as sacrificial templates for metal organic vapor phase epitaxy and chemical lift-off of GaN. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 071120	3.4	81
245	Large-Area Two-Dimensional Layered Hexagonal Boron Nitride Grown on Sapphire by Metalorganic Vapor Phase Epitaxy. <i>Crystal Growth and Design</i> , <b>2016</b> , 16, 3409-3415	3.5	81
244	. <i>IEEE Photonics Technology Letters</i> , <b>1993</b> , 5, 1288-1290	2.2	64
243	Bandgap energy bowing parameter of strained and relaxed InGaN layers. <i>Optical Materials Express</i> , <b>2014</b> , 4, 1030	2.6	63
242	Wafer-scale controlled exfoliation of metal organic vapor phase epitaxy grown InGaN/GaN multi quantum well structures using low-tack two-dimensional layered h-BN. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 171106	3.4	56
241	Microfabrication and optical study of reactive ion etched InGaAsP/InP and GaAs/GaAlAs quantum wires. <i>Applied Physics Letters</i> , <b>1990</b> , 56, 830-832	3.4	52
240	Self-induced laterally modulated GaInP/InAsP structure grown by metal-organic vapor-phase epitaxy. <i>Journal of Applied Physics</i> , <b>1994</b> , 75, 7881-7883	2.5	49
239	Monolithic integration of multiple-quantum-well lasers and modulators for high-speed transmission. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>1996</b> , 2, 326-335	3.8	47
238	Highly thermally stable, high-performance InGaAsP: InGaAsP multi-quantum-well structures for optical devices by atmospheric pressure MOVPE. <i>Journal of Crystal Growth</i> , <b>1992</b> , 124, 737-740	1.6	47
237	40-Gb/s tandem electroabsorption modulator. <i>IEEE Photonics Technology Letters</i> , <b>2002</b> , 14, 27-29	2.2	46
236	Investigation of the Performance of HEMT-Based NO, NO <sub>2</sub> and NH <sub>3</sub> Exhaust Gas Sensors for Automotive Antipollution Systems. <i>Sensors</i> , <b>2016</b> , 16, 273	3.8	44
235	Structural and compositional characterization of MOVPE GaN thin films transferred from sapphire to glass substrates using chemical lift-off and room temperature direct wafer bonding and GaN wafer scale MOVPE growth on ZnO-buffered sapphire. <i>Journal of Crystal Growth</i> , <b>2013</b> , 370, 63-67	1.6	42

234	Bandgap bowing in B <sub>GaN</sub> thin films. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 083118	3.4	42
233	Gas sensors boosted by two-dimensional h-BN enabled transfer on thin substrate foils: towards wearable and portable applications. <i>Scientific Reports</i> , <b>2017</b> , 7, 15212	4.9	41
232	Semibulk InGaN: A novel approach for thick, single phase, epitaxial InGaN layers grown by MOVPE. <i>Journal of Crystal Growth</i> , <b>2013</b> , 370, 57-62	1.6	41
231	GaN materials growth by MOVPE in a new-design reactor using DMHy and NH <sub>3</sub> . <i>Journal of Crystal Growth</i> , <b>2007</b> , 298, 428-432	1.6	40
230	Investigation of carrier heating and spectral hole burning in semiconductor amplifiers by highly nondegenerate four-wave mixing. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 2492-2494	3.4	40
229	Distributed Bragg reflectors based on diluted boron-based BAlN alloys for deep ultraviolet optoelectronic applications. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 051101	3.4	39
228	Flexible metal-semiconductor-metal device prototype on wafer-scale thick boron nitride layers grown by MOVPE. <i>Scientific Reports</i> , <b>2017</b> , 7, 786	4.9	35
227	Multilayered InGaN/GaN structure vs. single InGaN layer for solar cell applications: A comparative study. <i>Acta Materialia</i> , <b>2013</b> , 61, 6587-6596	8.4	35
226	B <sub>GaN</sub> materials on GaN/sapphire substrate by MOVPE using N <sub>2</sub> carrier gas. <i>Journal of Crystal Growth</i> , <b>2007</b> , 298, 316-319	1.6	34
225	Electroabsorption modulators for high-bit-rate optical communications: a comparison of strained InGaAs/InAlAs and InGaAsP/InGaAsP MQW. <i>Semiconductor Science and Technology</i> , <b>1995</b> , 10, 887-901	1.8	34
224	Very simple approach for high performance DFB laser-electroabsorption modulator monolithic integration. <i>Electronics Letters</i> , <b>1994</b> , 30, 1980-1981	1.1	34
223	Solar blind metal-semiconductor-metal ultraviolet photodetectors using quasi-alloy of B <sub>GaN</sub> /GaN superlattices. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 221101	3.4	33
222	Full polarization insensitivity of a 20 Gb/s strained-MQW electroabsorption modulator. <i>IEEE Photonics Technology Letters</i> , <b>1994</b> , 6, 1203-1206	2.2	32
221	Microbeam high-resolution x-ray diffraction in strained InGaAlAs-based multiple quantum well laser structures grown selectively on masked InP substrates. <i>Journal of Applied Physics</i> , <b>2005</b> , 97, 063512	2.5	31
220	BAlN thin layers for deep UV applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 745-750	1.6	30
219	MOVPE grown periodic AlN/BAlN heterostructure with high boron content. <i>Journal of Crystal Growth</i> , <b>2015</b> , 414, 119-122	1.6	30
218	Modeling and characterization of AlGaInAs and related materials using selective area growth by metal-organic vapor-phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2007</b> , 298, 28-31	1.6	30
217	. <i>IEEE Photonics Technology Letters</i> , <b>1992</b> , 4, 720-723	2.2	30

216	Experimental optimisation of MQW electroabsorption modulators with up to 40 GHz bandwidths. <i>Electronics Letters</i> , <b>1994</b> , 30, 1347-1348	1.1	29
215	Structural and optical properties of nanodots, nanowires, and multi-quantum wells of III-nitride grown by MOVPE nano-selective area growth. <i>Journal of Crystal Growth</i> , <b>2011</b> , 315, 160-163	1.6	28
214	Nanometer-scale, quantitative composition mappings of InGaN layers from a combination of scanning transmission electron microscopy and energy dispersive x-ray spectroscopy. <i>Nanotechnology</i> , <b>2012</b> , 23, 455707	3.4	27
213	Growth of GaN by metal organic vapor phase epitaxy on ZnO-buffered c-sapphire substrates. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 944-947	1.6	27
212	AlGaIn-based MQWs grown on a thick relaxed AlGaIn buffer on AlN templates emitting at 285 nm. <i>Optical Materials Express</i> , <b>2015</b> , 5, 380	2.6	26
211	Highly sensitive detection of NO <sub>2</sub> gas using BGaN/GaN superlattice-based double Schottky junction sensors. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 243504	3.4	26
210	Deep structural analysis of novel BGaN material layers grown by MOVPE. <i>Journal of Crystal Growth</i> , <b>2011</b> , 315, 288-291	1.6	26
209	MOVPE growth of transition-metal-doped GaN and ZnO for spintronic applications. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 5032-5038	1.6	26
208	Carrier transport limited bandwidth of 1.55 $\mu\text{m}$ quantum-well lasers. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 52-54	3.4	26
207	Experimental Study and Device Design of NO, NO <sub>2</sub> , and NH <sub>3</sub> Gas Detection for a Wide Dynamic and Large Temperature Range Using Pt/AlGaIn/GaN HEMT. <i>IEEE Sensors Journal</i> , <b>2016</b> , 16, 6828-6838	4	24
206	Dual-purpose BGaN layers on performance of nitride-based high electron mobility transistors. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 243503	3.4	24
205	Monolithic integration of InGaAsP-InP strained-layer distributed feedback laser and external modulator by selective quantum-well interdiffusion. <i>IEEE Photonics Technology Letters</i> , <b>1995</b> , 7, 1016-1018	1.8	24
204	20-Gb/s integrated DBR laser-EA modulator by selective area growth for 1.55- $\mu\text{m}$ WDM applications. <i>IEEE Photonics Technology Letters</i> , <b>1997</b> , 9, 898-900	2.2	23
203	Low-damage dry-etched grating on an MQW active layer and dislocation-free InP regrowth for 1.55- $\mu\text{m}$ complex-coupled DFB lasers fabrication. <i>IEEE Photonics Technology Letters</i> , <b>1998</b> , 10, 1070-1072	2.2	23
202	Experimental investigation of the relative importance of carrier heating and spectral-hole-burning on nonlinear gain in bulk and strained multi-quantum-well 1.55 $\mu\text{m}$ lasers. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 771-773	3.4	23
201	Interface state effects in GaN Schottky diodes. <i>Thin Solid Films</i> , <b>2012</b> , 522, 345-351	2.2	22
200	Effect of boron incorporation on growth behavior of BGaN/GaN by MOVPE. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 5058-5062	1.6	22
199	High power operation of phase-shifted DFB lasers with amplitude modulated coupling coefficient. <i>Electronics Letters</i> , <b>1992</b> , 28, 1395	1.1	22

198	Investigation of a relaxation mechanism specific to InGaN for improved MOVPE growth of nitride solar cell materials. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2012</b> , 209, 25-28	1.6	21
197	High temperature characteristic T0 and low threshold current density of 1.3 μm InAsP/InGaP/InP compensated strain multiquantum well structure lasers. <i>Electronics Letters</i> , <b>1995</b> , 31, 803-805	1.1	21
196	Model of Ni-63 battery with realistic PIN structure. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 105101	2.5	20
195	Characteristics of the surface microstructures in thick InGaN layers on GaN. <i>Optical Materials Express</i> , <b>2013</b> , 3, 1111	2.6	20
194	Electrical and structural characterizations of B GaN thin films grown by metal-organic vapor-phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2009</b> , 6, S1029-S1032		20
193	. <i>Journal of Lightwave Technology</i> , <b>1995</b> , 13, 1865-1872	4	20
192	Extremely uniform, reproducible growth of device quality InGaAsP:InP heterostructures in the T-shaped reactor at atmospheric pressure. <i>Journal of Crystal Growth</i> , <b>1988</b> , 93, 235-241	1.6	20
191	Role of compositional fluctuations and their suppression on the strain and luminescence of InGaN alloys. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 055705	2.5	19
190	High power operation of widely tunable 1.55 [micro sign]m distributed Bragg reflector laser. <i>Electronics Letters</i> , <b>1997</b> , 33, 210	1.1	19
189	High reliability of high-power and widely tunable 1.55-/spl mu/m distributed Bragg reflector lasers for WDM applications. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>1997</b> , 3, 607-614	3.8	19
188	20 GHz bandwidth 1.5 μm wavelength VUG DFB laser using a zero net strain In <sub>x</sub> Ga <sub>1-x</sub> As <sub>y</sub> P <sub>1-y</sub> well active structure grown at constant γ. <i>Electronics Letters</i> , <b>1993</b> , 29, 1290	1.1	19
187	1.55 μm multiquantum-well lasers with record performance obtained by atmospheric pressure MOVPE using organometallic phosphorus precursor. <i>Electronics Letters</i> , <b>1992</b> , 28, 1078	1.1	19
186	Efficient electroabsorption in InGaAsP/InGaAsP MQW optical waveguide. <i>Electronics Letters</i> , <b>1991</b> , 27, 1607	1.1	18
185	Improving InGaN heterojunction solar cells efficiency using a semibulk absorber. <i>Solar Energy Materials and Solar Cells</i> , <b>2017</b> , 159, 405-411	6.4	17
184	1.3 μm strain-compensated InAsP/InGaP electroabsorption modulator structure grown by atmospheric pressure metalorganic vapor epitaxy. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 96-98	3.4	17
183	Very low threshold and high power CW operation in 1.55 [micro sign]m gain-coupled DFB lasers with periodically etched quantum wells. <i>Electronics Letters</i> , <b>1997</b> , 33, 1881	1.1	17
182	Photonic integrated receiver for 40 Gbit/s transmission. <i>Electronics Letters</i> , <b>2002</b> , 38, 1196	1.1	17
181	Agile and fast switching monolithically integrated four wavelength selectable source at 1.55 μm. <i>IEEE Photonics Technology Letters</i> , <b>1999</b> , 11, 12-14	2.2	17

180	Microbeam high angular resolution x-ray diffraction in InGa <sub>0.5</sub> N <sub>0.5</sub> GaN selective-area-grown ridge structures. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 181926	3.4	16
179	Strain relaxation and surface migration effects in InGaAlAs and InGaAsP selective-area-grown ridge waveguides. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 081111	3.4	16
178	High-Quality InGaAsN Growth by Metalorganic Vapor-Phase Epitaxy Using Nitrogen Carrier Gas and Dimethylhydrazine, Tertiarybutylarsine as Group V Precursors. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, 1019-1021	1.4	16
177	Inhibition of thickness variations during growth of InAsP/InGaP and InAsP/InGaAsP multi-quantum wells with high compensated strains. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 2279-2281	3.4	16
176	Strained InGaAsP/InGaAsP/InAsP multi-quantum well structure for polarization insensitive electroabsorption modulator with high power saturation. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 4131-4132	3.4	16
175	Atmospheric pressure MOVPE growth of high performance polarisation insensitive strain compensated MQW InGaAsP/InGaAs optical amplifier. <i>Electronics Letters</i> , <b>1995</b> , 31, 1242-1244	1.1	16
174	Modeling, design, fabrication and experimentation of a GaN-based, <sup>63</sup> Ni betavoltaic battery. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 035101	3	15
173	Heterogeneous Integration of Thin-Film InGaN-Based Solar Cells on Foreign Substrates with Enhanced Performance. <i>ACS Photonics</i> , <b>2018</b> , 5, 3003-3008	6.3	15
172	Nanoscale selective area growth of thick, dense, uniform, In-rich, InGaN nanostructure arrays on GaN/sapphire template. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 163105	2.5	15
171	Mask pattern interference in AlGaInAs selective area metal-organic vapor-phase epitaxy: Experimental and modeling analysis. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 113113	2.5	15
170	Theoretical analysis of the influence of defect parameters on photovoltaic performances of composition graded InGaN solar cells. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2013</b> , 178, 142-148	3.1	14
169	Metal-organic vapour phase epitaxy of BInGaN quaternary alloys and characterization of boron content. <i>Journal of Crystal Growth</i> , <b>2010</b> , 312, 641-644	1.6	14
168	Selective area MOVPE growth of InP, InGaAs and InGaAsP using TBAs and TBP at different growth conditions. <i>Journal of Crystal Growth</i> , <b>1997</b> , 170, 645-649	1.6	14
167	TEM study of the morphological and compositional instabilities of InGaAsP epitaxial structures. <i>Journal of Crystal Growth</i> , <b>2000</b> , 221, 12-19	1.6	14
166	Efficient polarization insensitive electroabsorption modulator using strained InGaAsP-based quantum wells. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 3530-3532	3.4	14
165	State of the art 1.3 $\mu$ m lasers by atmospheric pressure MOVPE using tertiary butylphosphine. <i>Electronics Letters</i> , <b>1991</b> , 27, 1005-1006	1.1	14
164	InGaN/InGaN multiple-quantum-well grown on InGaN/GaN semi-bulk buffer for blue to cyan emission with improved optical emission and efficiency droop. <i>Superlattices and Microstructures</i> , <b>2017</b> , 104, 291-297	2.8	13
163	Nanoselective area growth and characterization of dislocation-free InGaN nanopramids on AlN buffered Si(111) templates. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 113105	3.4	13

162	Blue-violet boron-based Distributed Bragg Reflectors for VCSEL application. <i>Journal of Crystal Growth</i> , <b>2011</b> , 315, 283-287	1.6	13
161	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>1995</b> , 1, 371-374	3.8	13
160	Zero-loss multiple-quantum-well electroabsorption modulator with very low chirp. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 954-956	3.4	13
159	Taper-waveguide integration for polarisation insensitive InP/InGaAsP based optical amplifiers. <i>Electronics Letters</i> , <b>1994</b> , 30, 1290-1291	1.1	13
158	Wafer-scale epitaxial lift-off of optoelectronic grade GaN from a GaN substrate using a sacrificial ZnO interlayer. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 315105	3	12
157	Microstructural and electrical investigation of Pd/Au ohmic contact on p-GaN. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2015</b> , 33, 010603	1.3	12
156	Suppression of crack generation in AlGaIn/GaN distributed Bragg reflectors grown by MOVPE. <i>Journal of Crystal Growth</i> , <b>2013</b> , 370, 12-15	1.6	12
155	Design, Fabrication, and Characterization of Near-Milliwatt-Power RCLEDs Emitting at 390 nm. <i>IEEE Photonics Journal</i> , <b>2013</b> , 5, 8400709-8400709	1.8	12
154	Design, fabrication and physical analysis of TiN/AlN deep UV photodiodes. <i>Journal Physics D: Applied Physics</i> , <b>2010</b> , 43, 465104	3	12
153	Low temperature homoepitaxy of GaN by LP-MOVPE using Dimethylhydrazine and nitrogen. <i>Superlattices and Microstructures</i> , <b>2006</b> , 40, 476-482	2.8	12
152	20 Gbit/s high-performance integrated MQW TANDEM modulators and amplifier for soliton generation and coding. <i>IEEE Photonics Technology Letters</i> , <b>1995</b> , 7, 629-631	2.2	12
151	10 Gbit/s operation of polarisation insensitive, strained InGaAsP/InGaAsP MQW electroabsorption modulator. <i>Electronics Letters</i> , <b>1993</b> , 29, 1201	1.1	12
150	Very uniform epitaxy. <i>Progress in Crystal Growth and Characterization</i> , <b>1989</b> , 19, 39-49		12
149	Analytical formulations of image forces on dislocations with surface stress in nanowires and nanorods. <i>International Journal of Solids and Structures</i> , <b>2013</b> , 50, 4341-4348	3.1	11
148	Integrated multiquantum well distributed feedback laser-electroabsorption modulator with a negative chirp for zero bias voltage. <i>Electronics Letters</i> , <b>1997</b> , 33, 53	1.1	11
147	Study of growth rate and composition variations in metalorganic vapour phase selective area epitaxy at atmospheric pressure and application to the growth of strained layer DBR lasers. <i>Journal of Crystal Growth</i> , <b>1997</b> , 170, 639-644	1.6	11
146	Microbeam high-resolution diffraction and x-ray standing wave methods applied to semiconductor structures. <i>Journal Physics D: Applied Physics</i> , <b>2004</b> , 37, L9-L12	3	11
145	Carbon doping of InAlAs in LP-MOVPE using CBr <sub>4</sub> . <i>Journal of Crystal Growth</i> , <b>2000</b> , 221, 66-69	1.6	11

144	+55°C pulse lasing at 1.56 [micro sign]m of all-monolithic InGaAlAs/InP vertical cavity lasers. <i>Electronics Letters</i> , <b>1999</b> , 35, 811	1.1	11
143	Cation interdiffusion in InGaAsP/InGaAsP multiple quantum wells with constant P/As ratio. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 718-720	3.4	11
142	High-speed tandem of MQW modulators for coded pulse generation with 14-dB fiber-to-fiber gain. <i>IEEE Photonics Technology Letters</i> , <b>1996</b> , 8, 218-220	2.2	11
141	Exfoliation of AlN film using two-dimensional multilayer hexagonal BN for deep-ultraviolet light-emitting diodes. <i>Applied Physics Express</i> , <b>2019</b> , 12, 015505	2.4	11
140	High performance TiN gate contact on AlGaIn/GaN transistor using a mechanically strain induced P-doping. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 233506	3.4	10
139	The role of N <sub>2</sub> and H <sub>2</sub> as carrier gas on the selective area MOVPE of InP-based heterostructures using TBAs and TBP as group-V sources. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1997</b> , 44, 37-40	3.1	10
138	Synchrotron high angular resolution microdiffraction analysis of selective area grown optoelectronic waveguide arrays. <i>Journal Physics D: Applied Physics</i> , <b>2006</b> , 39, 1422-1426	3	10
137	MOVPE growth study of BxGa(1-x)N on GaN template substrate. <i>Superlattices and Microstructures</i> , <b>2006</b> , 40, 233-238	2.8	10
136	(InGa)(NAs)/GaAs structures emitting in 1.6 μm wavelength range. <i>Optical Materials</i> , <b>2001</b> , 17, 185-188	3.3	10
135	Suppression of fringe diffraction in localized holographic exposure for DFB laser arrays. <i>IEEE Photonics Technology Letters</i> , <b>1995</b> , 7, 721-723	2.2	10
134	Simple multiwavelength device fabrication technique using a single-grating holographic exposure. <i>IEEE Photonics Technology Letters</i> , <b>1996</b> , 8, 867-869	2.2	10
133	Large-Area van der Waals Epitaxial Growth of Vertical III-Nitride Nanodevice Structures on Layered Boron Nitride. <i>Advanced Materials Interfaces</i> , <b>2019</b> , 6, 1900207	4.6	9
132	Finite element modeling of dislocation in solids and its applications to the analysis of GaN nanostructures. <i>Computational Materials Science</i> , <b>2012</b> , 58, 154-161	3.2	9
131	1.55 [micro sign]m polarisation insensitive InGaAsP strained MQW optical amplifier integrated with short spot-size converters. <i>Electronics Letters</i> , <b>1996</b> , 32, 1403	1.1	9
130	GaN thin films on z- and x-cut LiNbO <sub>3</sub> substrates by MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 1565-1567		9
129	Step-bunching instability in strained-layer superlattices grown on vicinal substrates. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 306-308	3.4	9
128	Submilliwatt optical bistability in wafer fused vertical cavity at 1.55-μm wavelength. <i>IEEE Photonics Technology Letters</i> , <b>1996</b> , 8, 539-541	2.2	9
127	. <i>IEEE Photonics Technology Letters</i> , <b>1992</b> , 4, 1335-1338	2.2	9



126	Nanoselective area growth of GaN by metalorganic vapor phase epitaxy on 4H-SiC using epitaxial graphene as a mask. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 103105	3.4	9
125	Wafer-scale MOVPE growth and characterization of highly ordered h-BN on patterned sapphire substrates. <i>Journal of Crystal Growth</i> , <b>2019</b> , 509, 40-43	1.6	9
124	Novel Scalable Transfer Approach for Discrete III-Nitride Devices Using Wafer-Scale Patterned h-BN/Sapphire Substrate for Pick-and-Place Applications. <i>Advanced Materials Technologies</i> , <b>2019</b> , 4, 1900184	6.8	8
123	Barrier strain influence on the high-speed properties of compressively strained InGaAsP multi-quantum-well laser structures. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>1997</b> , 3, 330-335	3.8	8
122	New approach of Nano-Selective Area Growth (NSAG) for a precise control of GaN nanodots grown by MOVPE. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2008</b> , 147, 114-117	3.1	8
121	Micro-X-ray fluorescence and micro-photoluminescence in InGaAsP and InGaAs layers obtained by selective area growth. <i>Journal of Crystal Growth</i> , <b>2003</b> , 253, 38-45	1.6	8
120	Surface morphology, electrical and optical properties of In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP grown by metalorganic vapor-phase epitaxy using trimethylarsine and arsine. <i>Journal of Crystal Growth</i> , <b>1999</b> , 204, 1-9	1.6	8
119	. <i>IEEE Journal of Quantum Electronics</i> , <b>1991</b> , 27, 1794-1797	2	8
118	High-efficiency indium gallium nitride/Si tandem photovoltaic solar cells modeling using indium gallium nitride semibulk material: monolithic integration versus 4-terminal tandem cells. <i>Progress in Photovoltaics: Research and Applications</i> , <b>2016</b> , 24, 1436-1447	6.8	7
117	High quality thick InGaN nanostructures grown by nanoselective area growth for new generation photovoltaic devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 740-744	1.6	7
116	Analysis of Deep Level Defects in GaN p-i-n Diodes after Beta Particle Irradiation. <i>Electronics (Switzerland)</i> , <b>2015</b> , 4, 1090-1100	2.6	7
115	A study of B <sub>0.2</sub> GaN back-barriers for AlGaN/GaN HEMTs. <i>EPJ Applied Physics</i> , <b>2012</b> , 60, 30101	1.1	7
114	Tuning of internal gain, dark current and cutoff wavelength of UV photodetectors using quasi-alloy of B <sub>0.2</sub> GaN-GaN and B <sub>0.2</sub> GaN-AlN superlattices <b>2012</b> ,		7
113	Quantum well bandgap engineering for 1.5 $\mu$ m telecom applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2000</b> , 74, 66-69	3.1	7
112	Multiple distributed feedback operation at 1.55 $\mu$ m with uniform output powers in a single laser diode. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 600-602	3.4	7
111	Surface morphology of InGaAs and InP materials grown with trimethylarsenic and arsine on vicinal InP substrates. <i>Journal of Crystal Growth</i> , <b>1999</b> , 197, 755-761	1.6	7
110	Controlled disordering of compressively strained InGaAsP multiple quantum wells under SiO <sub>2</sub> :P encapsulant and application to laser-modulator integration. <i>Journal of Applied Physics</i> , <b>1995</b> , 78, 5638-5641	2.5	7
109	10 Gbit/s transmission experiment over 165 km of dispersive fibre using ASK-FSK modulation and direct detection. <i>Electronics Letters</i> , <b>1993</b> , 29, 973-975	1.1	7

108	Single crystalline boron rich B(Al)N alloys grown by MOVPE. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 042101	3.4	7
107	Polarization-Induced Electric Fields Make Robust n-GaN/i-InGaN/p-GaN Solar Cells. <i>IEEE Electron Device Letters</i> , <b>2013</b> , 34, 363-365	4.4	6
106	Analytical close-form solutions to the elastic fields of solids with dislocations and surface stress. <i>Philosophical Magazine</i> , <b>2013</b> , 93, 2497-2513	1.6	6
105	Low-loss hydrogenated buried waveguide coupler integrated with a four-wavelength distributive Bragg reflector laser array on InP. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 1750-1752	3.4	6
104	Accurate wavelength spacing from absorption-coupled DFB laser arrays. <i>IEEE Photonics Technology Letters</i> , <b>1997</b> , 9, 1316-1318	2.2	6
103	Effects of N doping on ZnO thin films grown by MOVPE. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 5011-5015	1.6	6
102	10 Gbit/s transmitter based on directly modulated InGaAlAs laser operating up to 126°C. <i>Electronics Letters</i> , <b>2003</b> , 39, 1653	1.1	6
101	Simultaneous demultiplexing and clock recovery of 80 Gb/s OTDM signals using a tandem electro-absorption modulator		6
100	Performance comparison of strained InGaNaNs/GaAs and InGaAs/GaAs QW laser diodes grown by MOVPE. <i>Electronics Letters</i> , <b>2000</b> , 36, 436	1.1	6
99	Room temperature laser operation of bulk InGaAsN/GaAs structures grown by AP-MOVPE using N <sub>2</sub> as carrier gas. <i>Electronics Letters</i> , <b>1999</b> , 35, 474	1.1	6
98	Polarization-independent filtering in a grating-assisted horizontal directional coupler. <i>IEEE Photonics Technology Letters</i> , <b>1995</b> , 7, 780-782	2.2	6
97	1.3 [micro sign]m InGaP/InAsP MQW lasers with large spot-size and low loss fibre chip coupling fabricated by a standard buried heterostructure process. <i>Electronics Letters</i> , <b>1996</b> , 32, 1582	1.1	6
96	Use of high purity trimethylindium-trimethylamine adduct in MOVPE of InP. <i>Journal of Crystal Growth</i> , <b>1992</b> , 124, 93-98	1.6	6
95	Effectiveness of selective area growth using van der Waals h-BN layer for crack-free transfer of large-size III-N devices onto arbitrary substrates. <i>Scientific Reports</i> , <b>2020</b> , 10, 21709	4.9	6
94	Role of V-pits in the performance improvement of InGaN solar cells. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 133507	3.4	6
93	Scalable control of graphene growth on 4H-SiC C-face using decomposing silicon nitride masks. <i>Journal Physics D: Applied Physics</i> , <b>2015</b> , 48, 152001	3	5
92	Structural and optical investigations of AlGaIn MQWs grown on a relaxed AlGaIn buffer on AlN templates for emission at 280 nm. <i>Journal of Crystal Growth</i> , <b>2015</b> , 432, 37-44	1.6	5
91	Emission wavelength red-shift by using $\beta$ -semi-bulk InGaIn buffer layer in InGaIn/InGaIn multiple-quantum-well. <i>Superlattices and Microstructures</i> , <b>2017</b> , 112, 279-286	2.8	5

90	Growth of Inhomogeneous ZnO nanostructures on Si(111), c-Al <sub>2</sub> O <sub>3</sub> , ZnO and steel substrates by pulsed laser deposition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2013</b> , 10, 1317-1321		5
89	Microstructural compositional, and optical characterization of GaN grown by metal organic vapor phase epitaxy on ZnO epilayers. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2009</b> , 27, 1655		5
88	Gain modeling of strained InGaAsP based MQW optical amplifiers. <i>IEEE Photonics Technology Letters</i> , <b>1997</b> , 9, 1475-1477	2.2	5
87	A new tunable laser using a single electroabsorption tuning super structure grating for subnanosecond switching applications. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>1997</b> , 3, 598-606	3.8	5
86	Phonons in Bx Ga <sub>1-x</sub> N/GaN epilayers studied by means of UV Raman scattering. <i>Physica Status Solidi (B): Basic Research</i> , <b>2008</b> , 245, 731-734	1.3	5
85	AlGa <sub>x</sub> N/AlN multiple quantum wells grown by MOVPE on AlN templates using nitrogen as a carrier gas. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 4927-4931	1.6	5
84	Residual stress relaxation in GaN/sapphire circular pillars measured by Raman scattering spectroscopy. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 5321-5326	1.6	5
83	Optical gain evaluation in GaInAsP quantum-well lasers: A comparison of the different growth techniques. <i>Journal of Applied Physics</i> , <b>1995</b> , 77, 821-826	2.5	5
82	Superimposed Bragg gratings on semiconductor material. <i>Electronics Letters</i> , <b>1996</b> , 32, 1884	1.1	5
81	Highly Ordered Boron Nitride/Epigraphene Epitaxial Films on Silicon Carbide by Lateral Epitaxial Deposition. <i>ACS Nano</i> , <b>2020</b> , 14, 12962-12971	16.7	5
80	MOVPE van der Waals epitaxial growth of AlGa <sub>x</sub> N/AlGa <sub>x</sub> N multiple quantum well structures with deep UV emission on large scale 2D h-BN buffered sapphire substrates. <i>Journal of Crystal Growth</i> , <b>2019</b> , 507, 352-356	1.6	5
79	Link between crystal quality and electrical properties of metalorganic vapour phase epitaxy In <sub>x</sub> Ga <sub>1-x</sub> N thin films. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 062113	3.4	4
78	Novel process for direct bonding of GaN onto glass substrates using sacrificial ZnO template layers to chemically lift-off GaN from c-sapphire <b>2012</b> ,		4
77	Submicron beam X-ray diffraction of nanoheteroepitaxially grown GaN: Experimental challenges and calibration procedures. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2010</b> , 268, 320-324	1.2	4
76	Tandem of modulators for high on/off pulse generation (85 dB). <i>Electronics Letters</i> , <b>1997</b> , 33, 1491	1.1	4
75	Lossless InAsP-InGaP modulator at 1.3 μm for optical conversion of radio signals up to 40 GHz. <i>IEEE Photonics Technology Letters</i> , <b>1997</b> , 9, 931-933	2.2	4
74	Tandem of electroabsorption modulators integrated with a DFB laser and an optical amplifier for short optical pulse generation and coding. <i>IEE Proceedings: Optoelectronics</i> , <b>1998</b> , 145, 198-200		4
73	Three-waveguide two-grating codirectional coupler for 1.3-/1.3+/1.5 [micro sign]m demultiplexing in transceiver. <i>Electronics Letters</i> , <b>2000</b> , 36, 2030	1.1	4

72	Wavelength accuracy in distributed phase-shifted DFB lasers. <i>IEEE Photonics Technology Letters</i> , <b>1999</b> , 11, 406-408	2.2	4
71	. <i>IEEE Photonics Technology Letters</i> , <b>1995</b> , 7, 185-187	2.2	4
70	High-speed InGaAsP/InGaAsP MQW electroabsorption modulator with high optical power handling capacity. <i>Electronics Letters</i> , <b>1992</b> , 28, 2157	1.1	4
69	Control of the Mechanical Adhesion of III-V Materials Grown on Layered h-BN. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2020</b> , 12, 55460-55466	9.5	4
68	Towards P-Type Conduction in Hexagonal Boron Nitride: Doping Study and Electrical Measurements Analysis of hBN/AlGaIn Heterojunctions. <i>Nanomaterials</i> , <b>2021</b> , 11,	5.4	4
67	Influence of barrier layer indium on efficiency and wavelength of InGaIn multiple quantum well (MQW) with and without semi-bulk InGaIn buffer for blue to green regime emission. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2017</b> , 214, 1600868	1.6	3
66	Core-shell GaN/nO moth-eye nanostructure arrays grown on a-SiO <sub>2</sub> /Si (1 1 1) as a basis for improved InGaIn-based photovoltaics and LEDs. <i>Photonics and Nanostructures - Fundamentals and Applications</i> , <b>2015</b> , 15, 53-58	2.6	3
65	Mask effect in nano-selective- area-growth by MOCVD on thickness enhancement, indium incorporation, and emission of InGaIn nanostructures on AlN-buffered Si(111) substrates. <i>Optical Materials Express</i> , <b>2017</b> , 7, 376	2.6	3
64	Comparison of chemical and laser lift-off for the transfer of InGaIn-based p-i-n junctions from sapphire to glass substrates <b>2013</b> ,		3
63	Selective growth of GaN nanodots and nanostripes on 6H-SiC substrates by metal organic vapor phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2009</b> , 6, S510-S513		3
62	Application of dilute boron B(Al,In,Ga)N alloys for UV light sources <b>2011</b> ,		3
61	Structural and morphological studies of GaN thin films grown on different oriented LiNbO <sub>3</sub> substrates by MOVPE. <i>EPJ Applied Physics</i> , <b>2008</b> , 43, 295-299	1.1	3
60	Micro-Raman for compositions characterization of selective area growth of Al <sub>x</sub> Ga <sub>1-x</sub> In <sub>1-x</sub> As materials by metal-organic vapor-phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 4741-4746	1.6	3
59	Accuracy on emitted wavelengths in DFB laser arrays resulting from the longitudinal mode selection mechanism. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2000</b> , 6, 191-196	3.8	3
58	Growth mode and effect of carrier gas on In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP surface morphology grown with trimethylarsine and arsine. <i>Applied Surface Science</i> , <b>1999</b> , 150, 161-170	6.7	3
57	An Optical Study of Interdiffusion in Strained InP-Based Heterostructures. <i>Japanese Journal of Applied Physics</i> , <b>1995</b> , 34, 36-41	1.4	3
56	Trimethylarsenic as an alternative to arsine in the metalorganic vapor phase epitaxy of device quality In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 209-211	3.4	3
55	Strained multi-quantum well heterostructures for lasers, modulators and integrated optical devices at 1.3 μm. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1994</b> , 28, 279-284	3.1	3

54	Large-area metal-organic vapour phase epitaxy for optoelectronic integrated circuits and photonics. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1991</b> , 9, 69-76	3.1	3
53	Monolithic Free-Standing Large-Area Vertical III-N Light-Emitting Diode Arrays by One-Step h-BN-Based Thermomechanical Self-Lift-Off and Transfer. <i>ACS Applied Electronic Materials</i> , <b>2021</b> , 3, 2614-2621	4.2	3
52	Evidence of minority carrier traps contribution in deep level transient spectroscopy measurement in n-GaN Schottky diode. <i>Superlattices and Microstructures</i> , <b>2017</b> , 101, 529-536	2.8	2
51	Nanopyramid-based absorber to boost the efficiency of InGaN solar cells. <i>Solar Energy</i> , <b>2019</b> , 190, 93-103	3.8	2
50	Chemical lift-off and direct wafer bonding of GaN/InGaN PIN structures grown on ZnO. <i>Journal of Crystal Growth</i> , <b>2016</b> , 435, 105-109	1.6	2
49	Nondestructive mapping of chemical composition and structural qualities of group III-nitride nanowires using submicron beam synchrotron-based X-ray diffraction. <i>Thin Solid Films</i> , <b>2013</b> , 541, 46-50	2.2	2
48	Dc and ac electrical response of MOCVD grown GaN in p-i-n structure, assessed through IV and admittance measurement. <i>Journal Physics D: Applied Physics</i> , <b>2017</b> , 50, 505109	3	2
47	Contribution to solar concentrators design for photovoltaic application <b>2014</b> ,		2
46	Modeling of polarization effects on n-GaN/i-InGaN/p-GaN solar cells with ultrathin GaN interlayers. <i>Optical and Quantum Electronics</i> , <b>2013</b> , 45, 681-686	2.4	2
45	Mechanism of Ohmic Cr/Ni/Au contact formation on p-GaN. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2012</b> , 30, 022205	1.3	2
44	Epitaxial MOVPE growth of highly c-axis oriented InGaN/GaN films on ZnO-buffered Si (111) substrates <b>2010</b> ,		2
43	InAsP/GaNP strained multilayers grown by MOVPE on (001), (113)B and (110) InP substrates: the role of the surface characteristics. <i>Microelectronics Journal</i> , <b>1997</b> , 28, 857-863	1.8	2
42	Tunable distributed Bragg reflector laser-electroabsorption modulator based on identical active layer monolithic integration approach. <i>Electronics Letters</i> , <b>1999</b> , 35, 1637	1.1	2
41	Multiple quantum well distributed feedback laser-electroabsorption modulator light source with 36 GHz		2
40	Mixing properties of a 20-GHz-bandwidth 1.5- $\mu$ m MQW DFB laser in Ku and Ka bands. <i>Microwave and Optical Technology Letters</i> , <b>1994</b> , 7, 57-60	1.2	2
39	Low threshold 1.5 $\mu$ m SCH-MQW lasers by atmospheric pressure MOVPE and direct comparison of low versus atmospheric pressure MOVPE laser growths. <i>Journal of Crystal Growth</i> , <b>1991</b> , 107, 761-766	1.6	2
38	Very simple approach for high performance tunable laser realisation. <i>Electronics Letters</i> , <b>1996</b> , 32, 2079	1.1	2
37	Integrated electroabsorption modulators for high speed transmission at 1.55 $\mu$ m. <i>European Physical Journal Special Topics</i> , <b>1999</b> , 09, Pr2-69		2

36	MOVPE of GaN-based mixed dimensional heterostructures on wafer-scale layered 2D hexagonal boron nitride. A key enabler of III-nitride flexible optoelectronics. <i>APL Materials</i> , <b>2021</b> , 9, 061101	5.7	2
35	Single-crystal nanopyramidal B GaN by nanoselective area growth on AlN/Si(111) and GaN templates. <i>Nanotechnology</i> , <b>2016</b> , 27, 115602	3.4	2
34	Nanoselective area growth of defect-free thick indium-rich InGaN nanostructures on sacrificial ZnO templates. <i>Nanotechnology</i> , <b>2017</b> , 28, 195304	3.4	1
33	Novel method for reclaim/reuse of bulk GaN substrates using sacrificial ZnO release layers <b>2014</b> ,		1
32	New generation of Distributed Bragg Reflectors based on BAlN/AlN structures for deep UV-optoelectronic applications <b>2011</b> ,		1
31	Asymmetrical design for non-relaxed near-UV AlGaIn/GaN distributed Bragg reflectors <b>2010</b> ,		1
30			1
29	Designing the relative impact of thickness/composition changes in selective area organometallic epitaxy for monolithic integration applications		1
28	Constant output power and low linewidth in a simple wide-tuning DFB laser with multiwavelength grating. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>1997</b> , 3, 628-631	3.8	1
27	Planar selective regrowth of high resistivity semi-insulating InP(Fe) by LP-MOVPE for buried lasers using TBP. <i>Journal of Crystal Growth</i> , <b>1998</b> , 195, 479-484	1.6	1
26	Progress on new wide bandgap materials B GaN, B GaAlN and their potential applications <b>2007</b> , 6479, 249		1
25	Integrated photonic devices for fiber optic communication systems		1
24	High quality InGaAsN growth by MOVPE using N/sub 2/ carrier gas and dimethylhydrazine, tertiarybutylarsine as group V precursors		1
23	Transform-limited pulses from low chirp DFB lasers with external feedback. <i>Electronics Letters</i> , <b>1993</b> , 29, 518	1.1	1
22	10 Gbit/s high performance MQW tandem modulator for soliton generation and coding. <i>Electronics Letters</i> , <b>1994</b> , 30, 1706-1707	1.1	1
21	Monolithic integration of multiple quantum well DFB lasers and electroabsorption modulators. <i>Microelectronics Journal</i> , <b>1994</b> , 25, 691-696	1.8	1
20	Novel high performance strained layer MQW monolithically integrated DFB laser-electroabsorption modulator using one identical single active layer		1
19	Tunable distributed Bragg reflector laser-electroabsorption modulator based on the identical active layer integration approach. <b>1999</b> ,		1

18	Sensors based on AlGaIn/GaN HEMT for fast H <sub>2</sub> and O <sub>2</sub> detection and measurement at high temperature <b>2019</b> ,		1
17	Experimental Determination of the Intraband Relaxation Time in Strained Quantum Well Lasers <b>1996</b> , 591-593		1
16	High performance strained MQW lasers at 1.3 μm by MOVPE using arsine generator system. <i>Electronics Letters</i> , <b>1994</b> , 30, 1681-1682	1.1	0
15	A new organoindium precursor for electronic materials. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1993</b> , 17, 34-40	3.1	0
14	Influence of Sapphire Substrate Orientation on the van der Waals Epitaxy of III-Nitrides on 2D Hexagonal Boron Nitride: Implication for Optoelectronic Devices. <i>ACS Applied Nano Materials</i> , <b>2022</b> , 5, 791-800	5.6	0
13	Epitaxial Graphene on SiC: 2D Sheets, Selective Growth, and Nanoribbons <b>2017</b> , 181-204		0
12	Natural Boron and B-Enriched Hexagonal Boron Nitride for High-Sensitivity Self-Biased Metal-Semiconductor-Metal Neutron Detectors.. <i>ACS Omega</i> , <b>2022</b> , 7, 804-809	3.9	0
11	Investigation of p-contact performance for indium rich InGaIn based light emitting diodes and solar cells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2017</b> , 214, 1600496	1.6	
10	Light-Emitting Diodes: Large-Area van der Waals Epitaxial Growth of Vertical III-Nitride Nanodevice Structures on Layered Boron Nitride (Adv. Mater. Interfaces 16/2019). <i>Advanced Materials Interfaces</i> , <b>2019</b> , 6, 1970102	4.6	
9	Heterogeneous Integration: Novel Scalable Transfer Approach for Discrete III-Nitride Devices Using Wafer-Scale Patterned h-BN/Sapphire Substrate for Pick-and-Place Applications (Adv. Mater. Technol. 10/2019). <i>Advanced Materials Technologies</i> , <b>2019</b> , 4, 1970057	6.8	
8	On the elastic field and image force of dislocations in anisotropic solids and its application to GaN nanostructures. <i>Philosophical Magazine</i> , <b>2014</b> , 94, 1235-1248	1.6	
7	Optimization of semibulk InGaIn-based solar cell using realistic modeling. <i>Solar Energy</i> , <b>2017</b> , 157, 687-698		
6	InGaP/InAsP MQW complex-coupled DFB taperless laser with large spot size and high coupling efficiency. <i>Electronics Letters</i> , <b>1997</b> , 33, 906	1.1	
5	Raman scattering study of B <sub>x</sub> Ga <sub>1-x</sub> N growth on AlN template substrate. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 3051-3053		
4	Application of X-ray standing wave (XSW) technique for studies of Zn incorporation in InP epilayers. <i>Computational Materials Science</i> , <b>2005</b> , 33, 132-135	3.2	
3	InGaAsP/AlGaAs multiple-wavelength vertical-cavity lasers and arrays in the 1.5-μm band fabricated by localized wafer fusion technique <b>2000</b> , 4068, 2		
2	Horizontal directional coupler filter suitable for integration in a 1.3+/1.3-μm duplexer. <i>Electronics Letters</i> , <b>1995</b> , 31, 2002-2003	1.1	
1	A cost-effective technology to improve power performance of nanoribbons GaN HEMTs. <i>Applied Physics Letters</i> , <b>2022</b> , 120, 042102	3.4	

